L	Hits	Search Text	DB	Time stamp
Number				
1	0	(variable adj resistane adj material) and	USPAT	2004/08/25
		memory and source and drain		09:37
2	3	(variable adj resistance adj material)	USPAT	2004/08/25
		and memory and source and drain		09:39
3	4	(variable adj resistance adj material)	US-PGPUB;	2004/08/25
	ļ	and memory and source and drain	EPO; JPO;	09:44
			DERWENT;	
			IBM_TDB	
4	182	(variable adj resistance) and memory and	US-PGPUB;	2004/08/25
		source and drain	EPO; JPO;	09:53
			DERWENT;	
_			IBM_TDB	
5	552	(variable adj resistance) and memory and	USPAT	2004/08/25
l _		source and drain		10:22
6	139	source and drain and chalcogenide	USPAT	2004/08/25
_				10:31
7	98	source and drain and chalcogenide	US-PGPUB;	2004/08/25
			EPO; JPO;	10:51
			DERWENT;	
			IBM_TDB	2004/00/25
8	9	pcram and memory	USPAT	2004/08/25
	-		ua Banun.	10:54
9	69	pcram and memory	US-PGPUB;	2004/08/25
			EPO; JPO;	10:54
			DERWENT;	
			IBM_TDB	

L	Hits	Search Text	DB	Time stamp
Number				
1	0	(variable adj resistane adj material) and	USPAT	2004/08/25
		memory and source and drain		09:37
2	3	(variable adj resistance adj material)	USPAT	2004/08/25
		and memory and source and drain		09:39
3	4	(variable adj resistance adj material)	US-PGPUB;	2004/08/25
		and memory and source and drain	EPO; JPO;	09:44
ţ			DERWENT;	
			IBM_TDB	
4	182	(variable adj resistance) and memory and	US-PGPUB;	2004/08/25
1		source and drain	EPO; JPO;	09:53
			DERWENT;	
			IBM TDB	
5	552	(variable adj resistance) and memory and	USPAT	2004/08/25
		source and drain		09:53